APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention

[METHOD FOR FABRICATING A MOSFET AND REDUCING LINE

WIDTH OF GATE STRUCTURE

Application Type: regular, utility
Attorney Docket Number: 11760-US-PA

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as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.